Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	795	(438/787).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:07
L2	574	(438/788).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:07
L3	349	(438/789).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:07
L4	280	(438/792).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:14
L5	1371	(438/197).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:08
L6	1128	(438/287).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:11
L7	1371	(438/197).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:11
L8	345	(438/216).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:11
L9	454	(438/791).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:14
L10	341	(438/775).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:15
S1	765	(438/787).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:15

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C:\Documents and Settings\tle10\My Documents\EAST\Workspaces\FET, MOS, IGFET, DMOS\10809809 Fujitsu nitridation SiO gate 4

S2	553	(438/788).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:07
S3	338	(438/789).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:07
S4	376	(438/790).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:07
S5	425	(438/791).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:08
S6	265	(438/792).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:08
S7	50	(438/793).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 09:45
S8	53	(438/794).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2005/08/03 09:46
S9	1256	(438/197).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:08
S10	1071	(438/287).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:08
S11	0	@ad<="20040326" and (FET or transistor) and 'LDD' and 'gate insulating' same ('silicon oxide or dioxide') with 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 10:51
S12	0	@ad<="20040326" and 'gate insulating' same ('silicon oxide or dioxide') with 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 09:49

S13	0	@ad<="20040326" and (FET or transistor) and 'LDD' and 'gate insulating' same 'silicon oxide' with 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 09:50
S14	71	@ad<="20040326" and 'silicon oxide' near 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 10:28
S15	2	("6780720").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 10:15
S16	1	"6566205".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:16
S17	1	"6444592".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:16
S18	1	"6380104".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:18
S19	1	"6380056".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:19
S20	1	"629 _. 1867".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:21
S21	1	"6255204".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:21
S22	1	"6251761".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:22
S23	1	"6251729".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:23
S24	1	"6228721".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:24
S25	1	"6110784".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:24
S26	1	"6087208".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:25
S27	2	("6667251").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 10:33
S28	1	"5685949".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:29
S29	1	"6281138".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:29
S30	1	"20020197884".PN.	US-PGPUB	OR	ON	2005/08/03 10:29

S31	2	("5656516").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 10:33
S32	. 1	"6444592".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:48
S33	1	"6372581".PN.	USPAT; USOCR	OR	ON	2005/08/03 10:49
S34	0	@ad<="20040326" and 'silicon oxide' same 'nitrogen' with (replacing' or displacing') with 'silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 10:52
S35	85	@ad<="20040326" and 'silicon oxide' same 'nitrogen' with (replac\$3' or displac\$3') with 'silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 10:52
S36	2	("6136654").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 16:02
S37	2	"20040251495"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 16:02